封装形式/package structure : SOP8

型号/TYPE：SLS4606A

The SLS4606A uses advanced trench technology to provide excellent RDS(ON) and low gate charge . The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

SLS4606A采用先进的沟槽技术，提供卓越的无线电数据系统（ON）和低栅电荷。互补mosfet可用于形成电平移位的高压侧开关，以及用于许多其它应用。

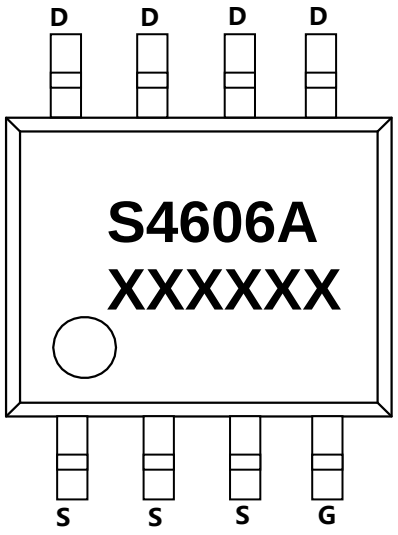
主要特性/Features

先进的沟槽工艺技术 Advanced trench process technology
高密度单元设计，超低导通电阻 High density cell design for ultra low on-resistance
高功率和电流处理能力 High power and current handing capability
适用于锂电池组应用 Ideal for Liion battery pack applications
N+P Channel Power MOSFET N+P沟道功率mosfet

应用/Application

消费电子产品 Consumer electronics

印字/MARKING 引脚定义/pin definition



N沟道极限参数/N-Channel Absolute maximum ratings(Ta=25℃)

参数Parameter	符号Symbol	数值Value	单位Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	5.0	A
Pulsed Drain Current (note1)	I_{DM}	20	A
Power Dissipation	P_D (Ta=25℃)	1.15	W
Thermal Resistance Junction to Ambient(note2)	$R_{\theta JA}$	100	℃/mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～150	℃

N沟道电性能参数/ P-Channel Electrical characteristics (Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
静态参数/Static Characteristics						
Drain-Source Breakdown Voltage	$V_{BR(DSS)}$	V_{GS}=0V,I_D=250μ A	30			V
Gate Threshold Voltage(note3)	$V_{GS(th)}$	I_D=250μ A, V_{GS}=V_{DS}	1		3	V
Gate-body leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS}=24V,V_{GS}=0V			1	μA
Drain-source on-resistance(note3)	$R_{DS(ON)}$	V_{GS}=10V,I_D=5A			32	mΩ
		V_{GS}=4.5V,I_D=4A			40	
Drain-Source Diode Forward Voltage(note3)	V_{SD}	V_{GS} = 0V, I_{SD} = 3A	0.5		1.2	V
动态参数/Dynamic Characteristics(note4)						
Input Capacitance	C_{iss}	V_{DS}=10V, V_{GS}=0V, f=1MHz		620		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			80		
开关参数/Switching Characteristics(note4)						
Turn-on delay t ime	$t_{d(on)}$	V_{DD}=15V,I_{DS}=1A , V_{GEN}=4.5V,R_L=15Ω , R_{GEN}=6Ω ,			35	ns
Turn-on rise time	t_r				55	ns
Turn-off delay time	$t_{d(off)}$				75	ns
Turn-off fall time	t_f				30	ns

P沟道极限参数/P-Channel Absolute maximum ratings(Ta=25℃)

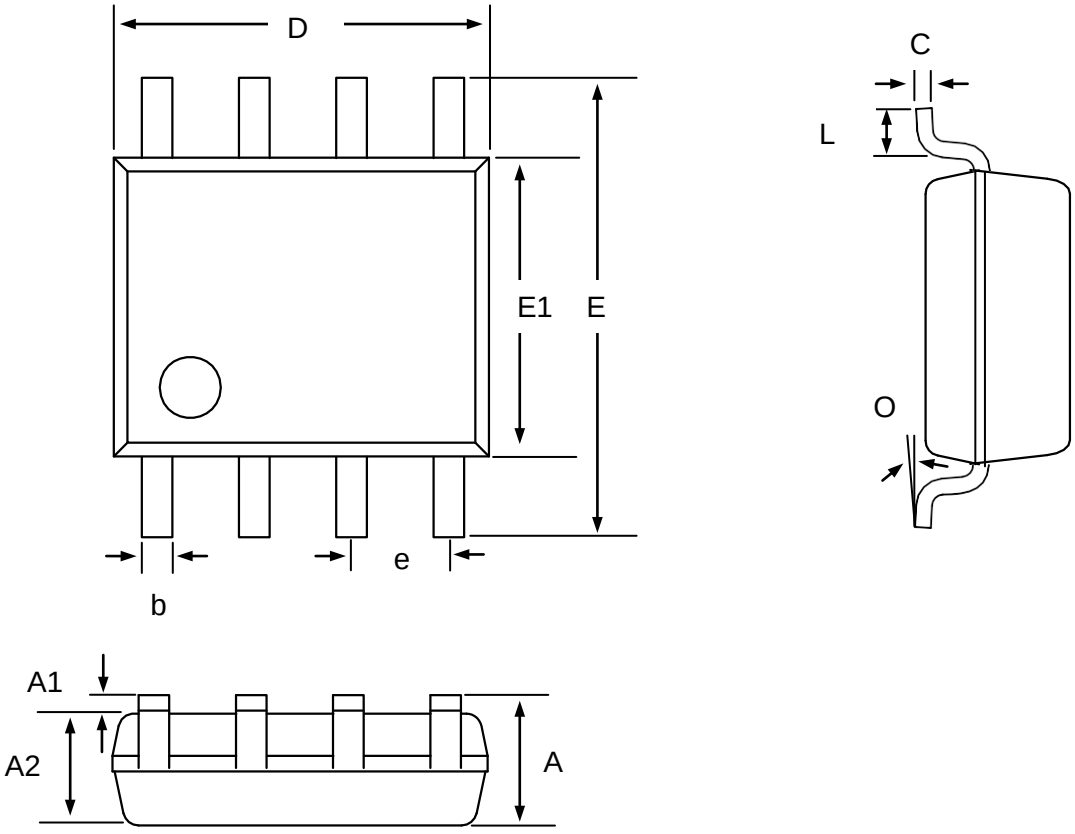
参数Parameter	符号Symbol	数值Value	单位Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-5.0	A
Pulsed Drain Current (note1)	I_{DM}	-20	A
Power Dissipation	P_D (Ta=25℃)	1.15	W
Thermal Resistance Junction to Ambient(note2)	$R_{\theta JA}$	100	℃/mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～150	℃

P沟道电性能参数/ P-Channel Electrical characteristics (Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
静态参数/Static Characteristics						
Drain-Source Breakdown Voltage	$V_{BR(DSS)}$	V_{GS}=0V,I_D=-250μ A	-30			V
Gate Threshold Voltage(note3)	$V_{GS(th)}$	I_D=250μ A, V_{GS}=V_{DS}	-1		-3	V
Gate-body leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V			-1	μA
Drain-source on-resistance(note3)	$R_{DS(ON)}$	V_{GS}=-10V,I_D=-5A			55	mΩ
		V_{GS}=-4.5V,I_D=-4A			90	
Drain-Source Diode Forward Voltage(note3)	V_{SD}	V_{GS} = 0V, I_{SD} = -3A	-0.5		-1.2	V
动态参数/Dynamic Characteristics(note4)						
Input Capacitance	C_{iss}	V_{DS}=-10V, V_{GS}=0V, f=1MHz		620		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			80		
开关参数/Switching Characteristics(note4)						
Turn-on delay t ime	$t_{d(on)}$	V_{DD}=-15V,I_{DS}=-1A , V_{GEN}=-4.5V,R_L=15Ω , R_{GEN}=6Ω ,			35	ns
Turn-on rise time	t_r				55	ns
Turn-off delay time	$t_{d(off)}$				75	ns
Turn-off fall time	t_f				30	ns

封装形式/package structure : SOP8

封装外观尺寸/SOP8 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270(BSC)		
E	3.800	3.900	4.000
E1	0.400	0.835	1.2700
L	0°	4°	8°